



BUK956R1-100E,127 Information

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For Reference Only

Part Number BUK956R1-100E,127

Manufacturer NXP

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 120A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BUK956R1-100E,127 Specifications

| Manufacturer Part Number BUK956R1-100E,127 Manufacturer NXP Category Discrete Semiconductor Products | | |
|--|--|--------------------------------------|
| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 133nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 17460pF @ 25V Vgs (Max) #10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 199 | Manufacturer Part Number | BUK956R1-100E,127 |
| Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 133nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 17460pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 349W (Tc) Rds On (Max) @ Id, Vgs 5.9 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Manufacturer | NXP |
| Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 133nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 17460pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 349W (Tc) Rds On (Max) @ Id, Vgs 5.9 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Category | Discrete Semiconductor Products |
| SeriesTrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2.1V @ 1mAGate Charge (Qg) (Max) @ Vgs133nC @ 5VInput Capacitance (Ciss) (Max) @ Vds17460pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)349W (Tc)Rds On (Max) @ Id, Vgs5.9 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | | Transistors - FETs, MOSFETs - Single |
| FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 133nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 17460pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 349W (Tc) Rds On (Max) @ Id, Vgs 5.9 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 70-220AB Package / Case 7100 Table 100V | Package | TO-220-3 |
| Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case MOSFET (Metal Oxide) 100V **MOSFET (Metal Oxide) 100V **ET (Metal Oxide) 120A (Tc) 120A (Tc) 120A (Tc) 121A (Td) 121A (Td) 122A (Tc) 123A (Tc) 123A (Td) 124A (Tc) 124A (Tc) 125A (Td) 126A (Tc) 126A (Tc) 126A (Tc) 126A (Tc) 127A (Td) 127A | Series | TrenchMOS? |
| Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 100V 120A (Tc) 133nC @ 5V 17460pF @ 25V 17460pF @ 25V 17460pF @ 25V 175V 176V 1776 (TJ) 1770 (TJ) 1780 (TJ) 1780 (TO-220AB 170-220-3 | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Son (Max) @ Id, Vgs Toperating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 120A (Tc) 120A (T | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Son (Max) @ Id, Vgs Through Hole Supplier Device Package Package / Case Sun (Max) & 5V, 10V 2.1V @ 1mA 1.33nC @ 5V 1.7460pF @ 25V 1.7460pF @ | Drain to Source Voltage (Vdss) | 100V |
| Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 133nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 17460pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 349W (Tc) Rds On (Max) @ Id, Vgs 5.9 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Current - Continuous Drain (Id) @ 25°C | 120A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jemperature Through Hole Supplier Device Package TO-220AB Package / Case 133nC @ 5V 17460pF @ 25V 17460pF | Drive Voltage (Max Rds On, Min Rds On) | 5V, 10V |
| Input Capacitance (Ciss) (Max) @ Vds 17460pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.9 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Vgs(th) (Max) @ Id | 2.1V @ 1mA |
| Vgs (Max)±10VFET Feature-Power Dissipation (Max)349W (Tc)Rds On (Max) @ Id, Vgs5.9 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | Gate Charge (Qg) (Max) @ Vgs | 133nC @ 5V |
| FET Feature - Graduate - FET Feature - Supplier Device Package / Case - Graduate - Gradu | Input Capacitance (Ciss) (Max) @ Vds | 17460pF @ 25V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.9 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Vgs (Max) | ±10V |
| Rds On (Max) @ Id, Vgs5.9 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Power Dissipation (Max) | 349W (Tc) |
| Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Rds On (Max) @ Id, Vgs | 5.9 mOhm @ 25A, 10V |
| Supplier Device Package TO-220AB Package / Case TO-220-3 | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case TO-220-3 | Mounting Type | Through Hole |
| | Supplier Device Package | TO-220AB |
| Report errors? | Package / Case | TO-220-3 |
| | | Report errors? |

BUK956R1-100E,127 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BUK956R1-100E,127 Payment Methods



















BUK956R1-100E,127 Shipping Methods













If you have any question about BUK956R1-100E,127, please do not hesitate to contact us!

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